

|           | <b>Hit<br/>s</b> | <b>Search Text</b>   | <b>DBs</b>  |
|-----------|------------------|--|---|
| <b>29</b> | 2                | S27 and S28  | US-PGPUB;<br>USPAT; FPRS;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB |
| <b>30</b> | 9                | ((substrate or wafer) same (ITO or (transparent near4 conductive near6 layer)) same (resist or photoresist) same (methacrylate or acrylate or polycarbonate or polyimide) same (lithography or expos\$4 or irradiat\$4 or illuminat\$4) same develop\$4 same (etch\$4 near28 (dry or RIE)))                                    | US-PGPUB;<br>USPAT; FPRS;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB |
| <b>31</b> | 18               | ((substrate or wafer) same (ITO or (transparent near4 conductive near6 layer) or (indium near4 tin near4 oxide)) same (resist or photoresist) same (methacrylate or acrylate or polycarbonate or polyimide) same (lithography or expos\$4 or irradiat\$4 or illuminat\$4)) and (develop\$4 same (etch\$4 near28 (dry or RIE))) | US-PGPUB;<br>USPAT; FPRS;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB |
| <b>32</b> | 288              | ((substrate or wafer) same (ITO or (transparent near4 conductive near6 layer) or (indium near4 tin near4 oxide)) same (resist or photoresist) same (lithography or expos\$4 or irradiat\$4 or illuminat\$4)) and (develop\$4 same (etch\$4 near28 (dry or RIE)))   | US-PGPUB;<br>USPAT; FPRS;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB |
| <b>33</b> | 185<br>58        | ((resist or photoresist) near26 (acrylate or methacrylate or polycarbonate or polyimide))  | US-PGPUB;<br>USPAT; FPRS;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB |

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|-----------|------------------|--------------------|---|
| <b>34</b> | 34               | S32 and S33        | US-PGPUB;<br>USPAT; FPRS;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB |